

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBU0230-N(Lead-free Device)

I_o = 200 mA

V_R = 30 Volts



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low drop-down voltage.

Majority carrier conduction.

Mechanical data

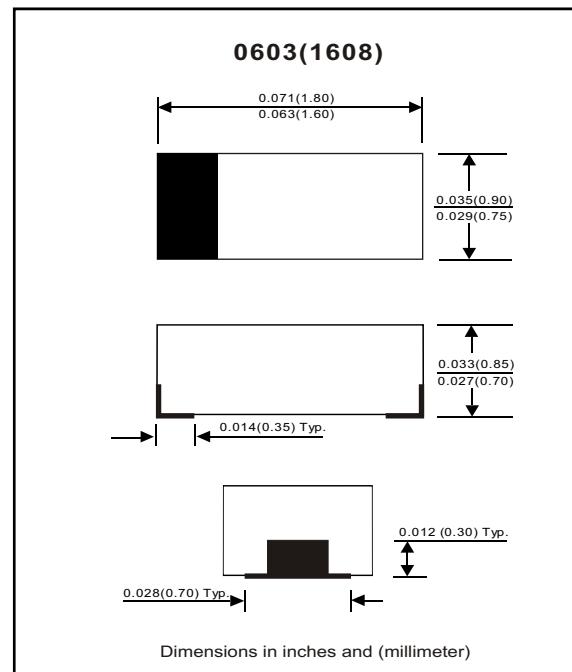
Case: 0603 (1608) Standard package , molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band

Mounting position: Any.

Weight: 0.003 gram (approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			35	V
Reverse voltage		V _R			30	V
Average forward current		I _o			200	mA
Forward current,surge peak	8.3ms single halfsine-wave superimposed on rate load(JEDEC method)	I _{FSM}		2000		mA
Power Dissipation		P _D			150	mW
Storage temperature		T _{STG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 200 mADC	V _F			0.50	V
Reverse current	V _R = 30 V	I _R			30	uA
Capacitance between terminals	f = 1 MHz, and 10VDC reverse voltage	C _T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBU0230-N)

Fig. 1 - Forward characteristics

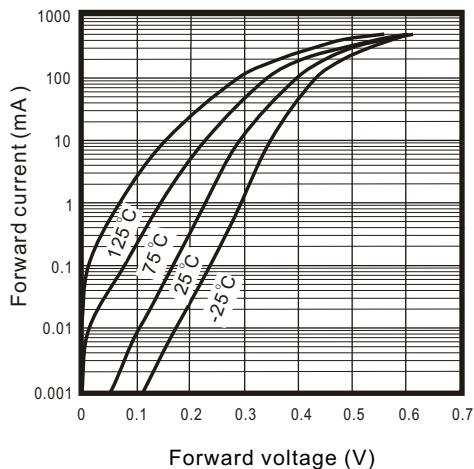


Fig. 2 - Reverse characteristics

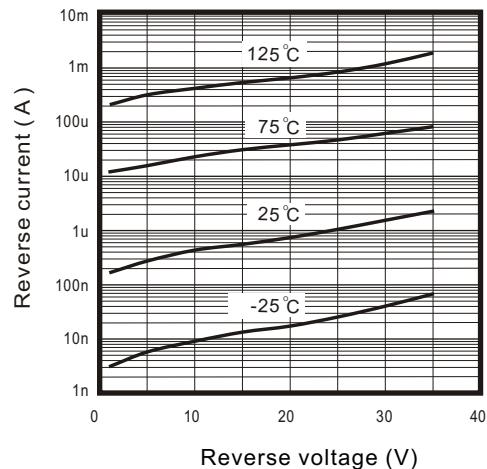


Fig. 3 - Capacitance between terminals characteristics

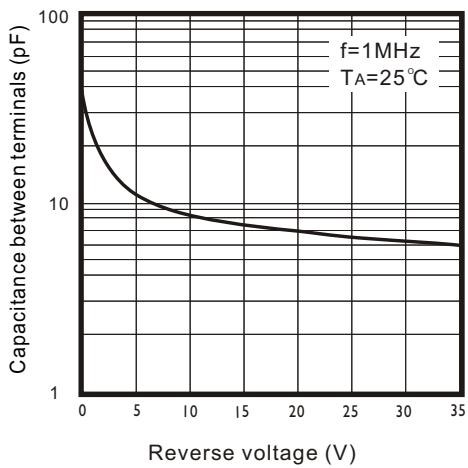


Fig. 4 - Current derating curve

